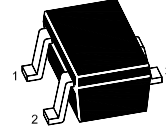


NPN Silicon Epitaxial Planar Transistor

for general purpose and switching applications



1.Base 2.Emitter 3.Collector
SOT-323 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage BC846W BC847W BC848W BC849W BC850W	V_{CBO}	80 50 30 30 50	V
Collector Emitter Voltage BC846W BC847W BC848W BC849W BC850W	V_{CEO}	65 45 30 30 45	V
Emitter Base Voltage BC846W BC847W BC848W BC849W BC850W	V_{EBO}	6 6 5 5 5	V
Collector Current	I_C	100	mA
Peak Collector Current	I_{CM}	200	mA
Total Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$



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SOT-323



BC846W-BC850W

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Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit	
DC Current Gain at $V_{CE} = 5\text{ V}$, $I_C = 2\text{ mA}$	BC846AW~BC850AW	h_{FE}	110	220	-
	BC846BW~BC850BW	h_{FE}	200	450	-
	BC846CW~BC850CW	h_{FE}	420	800	-
Collector Base Voltage at $I_C = 10\text{ }\mu\text{A}$	BC846W	V_{CBO}	80	-	V
	BC847W		50	-	
	BC848W		30	-	
	BC849W		30	-	
	BC850W		50	-	
Collector Emitter Voltage at $I_C = 10\text{ mA}$	BC846W	V_{CEO}	65	-	V
	BC847W		45	-	
	BC848W		30	-	
	BC849W		30	-	
	BC850W		45	-	
Emitter Base Voltage at $I_E = 1\text{ }\mu\text{A}$	BC846W	V_{EBO}	6	-	V
	BC847W		6	-	
	BC848W		5	-	
	BC849W		5	-	
	BC850W		5	-	
Collector Base Cutoff Current at $V_{CB} = 30\text{ V}$	I_{CBO}	-	15	nA	
Emitter Base Cutoff Current at $V_{EB} = 5\text{ V}$	I_{EBO}	-	100	nA	
Collector Emitter Saturation Voltage at $I_C = 10\text{ mA}$, $I_B = 0.5\text{ mA}$ $I_C = 100\text{ mA}$, $I_B = 5\text{ mA}$	$V_{CE(sat)}$	-	0.25	V	
		-	0.6		
Base Emitter Voltage at $V_{CE} = 5\text{ V}$, $I_C = 2\text{ mA}$ $V_{CE} = 5\text{ V}$, $I_C = 10\text{ mA}$	V_{BE}	0.58	0.7	V	
		-	0.77		
Transition Frequency at $V_{CE} = 5\text{ V}$, $I_C = 10\text{ mA}$, $f = 100\text{ MHz}$	f_T	100	-	MHz	
Collector Output Capacitance at $V_{CB} = 10\text{ V}$, $I_E = 0$, $f = 1\text{ MHz}$	C_{ob}	-	4.5	pF	

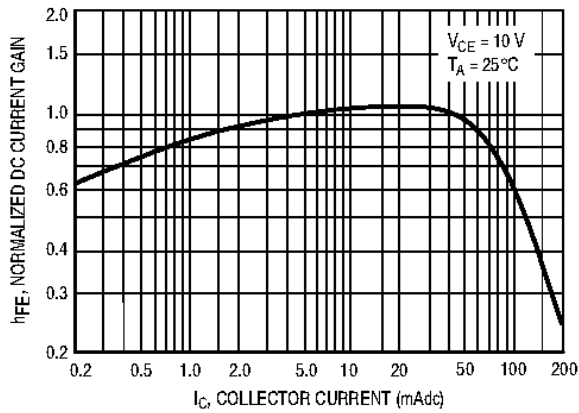


Figure 1. Normalized DC Current Gain

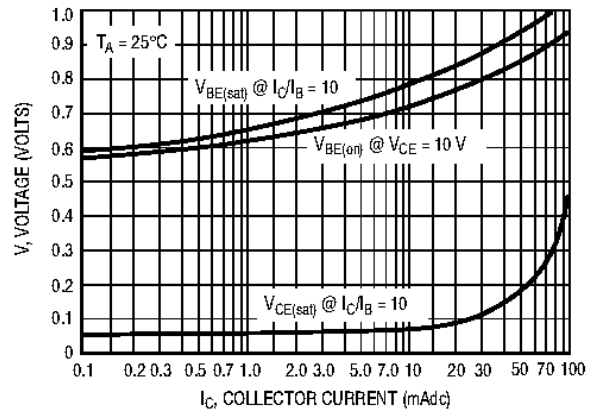


Figure 2. "Saturation" and "On" Voltages

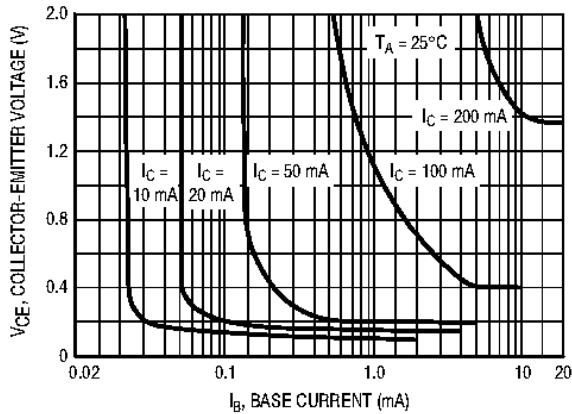


Figure 3. Collector Saturation Region

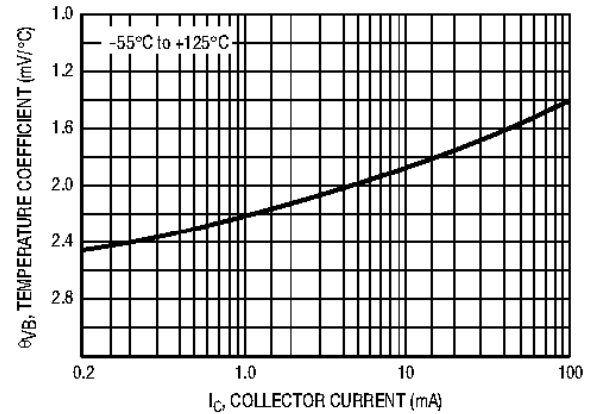


Figure 4. Base-Emitter Temperature Coefficient

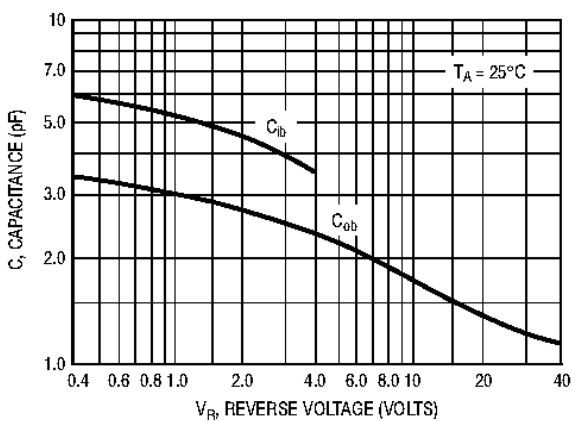


Figure 5. Capacitances

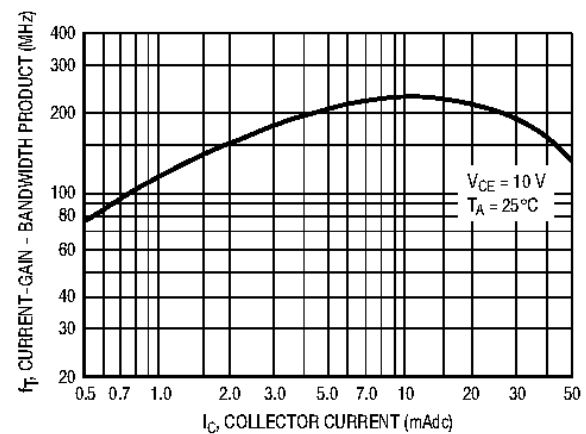


Figure 6. Current-Gain - Bandwidth Product

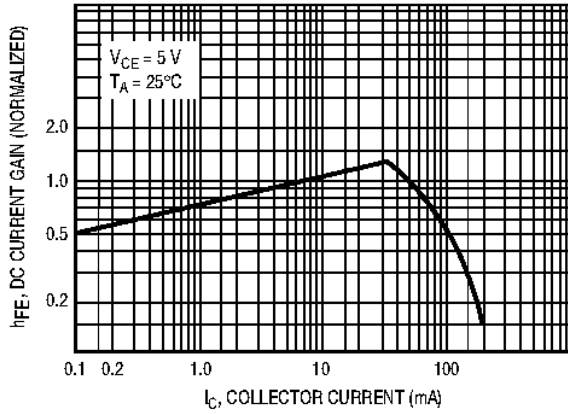


Figure 7. DC Current Gain

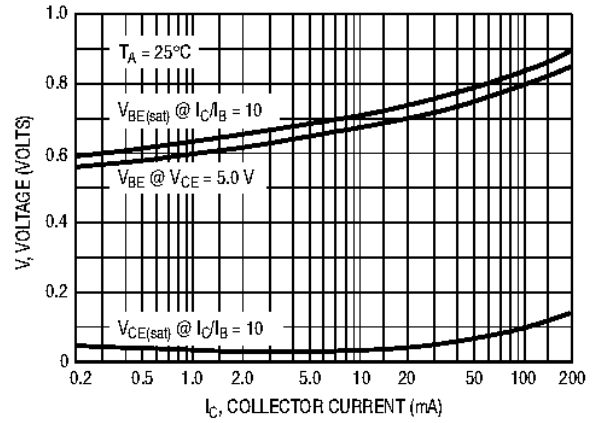


Figure 8. "On" Voltage

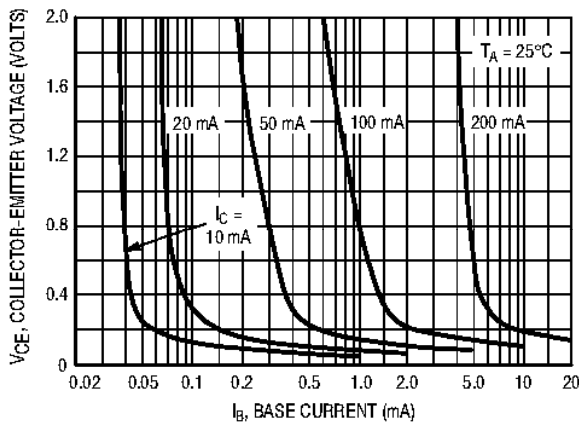


Figure 9. Collector Saturation Region

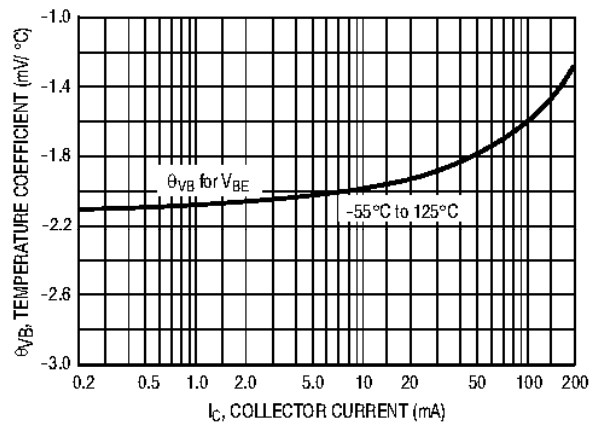


Figure 10. Base-Emitter Temperature Coefficient

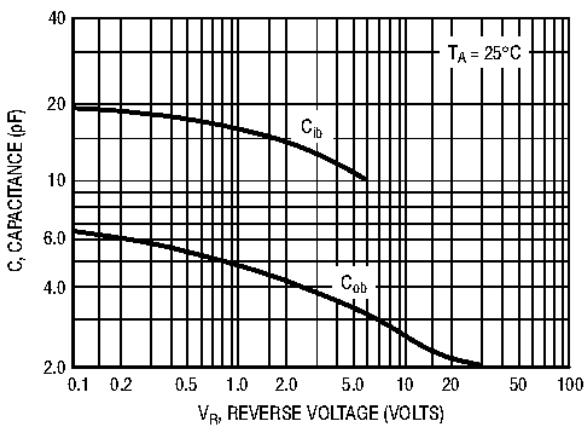


Figure 11. Capacitance

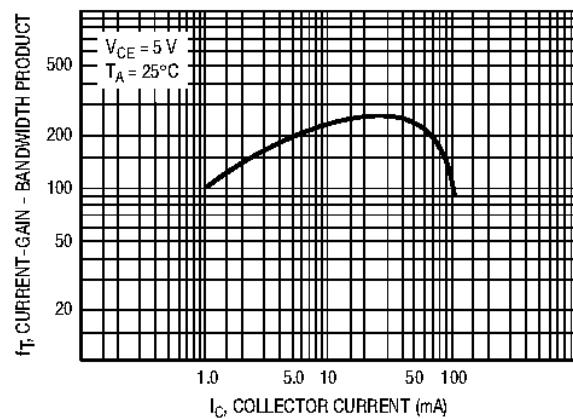


Figure 12. Current-Gain - Bandwidth Product



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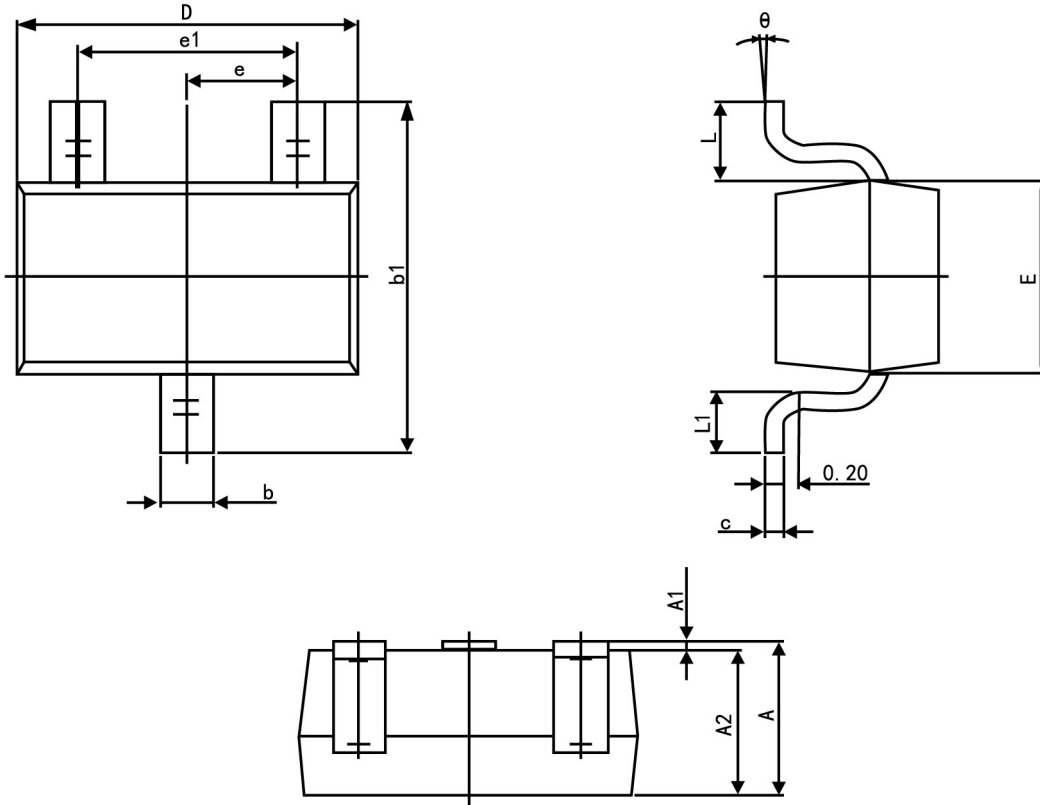
SOT-323



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SOT-323 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimension in Millimeters	
	Min	Max
A	0.900	1.100
A1	0.000	0.100
A2	0.900	1.000
b	0.200	0.400
c	0.080	0.150
D	2.000	2.200
E	1.150	1.350
E1	2.150	2.450
e	0.650 TYP.	
e1	1.200	1.400
L	0.525 REF.	
L1	0.260	0.460
theta	0°	8°